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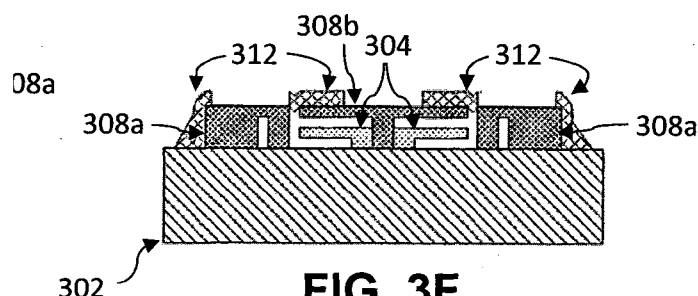
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(54) **Title:** THIN FILM ENCAPSULATION OF ELECTRODES



(57) **Abstract:** A method of fabricating encapsulated microelectromechanical system (MEMS) devices, comprising: providing a substrate having one or more MEMS devices formed thereon; depositing a sacrificial layer over the substrate and the one or more MEMS devices; patterning the sacrificial layer to define one or more cavities in the sacrificial layer and around the one or more MEMS devices; forming a cap layer over the sacrificial layer and the one or more cavities, the cap layer having one or more etch holes defined therein; removing the sacrificial layer by etching the sacrificial layer at least through the one or more etch holes; and depositing a sealing layer over the cap layer and the one or more etch holes to encapsulate the one or more MEMS devices, the substrate, and the cap layer.

